INTEGRATED CIRCUITS

DATA SHEET

74ABT126Quad buffer (3-State)

Product specification Supersedes data of 1996 Feb 26 IC23 Data Handbook





Quad buffer (3-State)

74ABT126

FEATURES

- Quad bus interface
- 3-State buffers
- Live insertion/extraction permitted
- Output capability: +64mA/-32mA
- Latch-up protection exceeds 500mA per JEDEC Std 17
- ESD protection exceeds 2000V per MIL STD 883 Method 3015 and 200V per Machine Model
- Power-up 3-State
- Inputs are disabled during 3-State mode

DESCRIPTIONThe 74ABT126 high

The 74ABT126 high-performance BiCMOS device combines low static and dynamic power dissipation with high speed and high output drive.

The 74ABT126 device is a quad buffer that is ideal for driving bus lines. The device features four Output Enables (OE0, OE1, OE2, OE3), each controlling one of the 3-State outputs.

QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS T _{amb} = 25°C; GND = 0V	TYPICAL	UNIT
t _{PLH} t _{PHL}	Propagation delay An to Yn	$C_L = 50pF; V_{CC} = 5V$	2.9	ns
C _{IN}	Input capacitance	$V_I = 0V \text{ or } V_{CC}$	4	pF
C _{OUT}	Output capacitance	Outputs disabled; V _O = 0V or V _{CC}	7	pF
I _{CCZ}	Total supply current	Outputs disabled; V _{CC} = 5.5V	65	μΑ

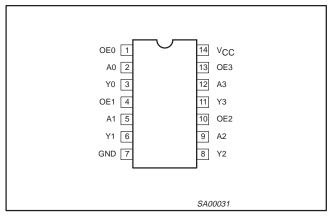
ORDERING INFORMATION

PACKAGES	TEMPERATURE RANGE	OUTSIDE NORTH AMERICA	NORTH AMERICA	DWG NUMBER
14-Pin Plastic DIP	-40°C to +85°C	74ABT126 N	74ABT126 N	SOT27-1
14-Pin plastic SO	–40°C to +85°C	74ABT126 D	74ABT126 D	SOT108-1
14-Pin Plastic SSOP Type II	-40°C to +85°C	74ABT126 DB	74ABT126 DB	SOT337-1
14-Pin Plastic TSSOP Type I	-40°C to +85°C	74ABT126 PW	74ABT126PW DH	SOT402-1

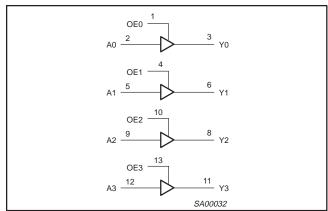
PIN DESCRIPTION

PIN NUMBER	SYMBOL	NAME AND FUNCTION
2, 5, 9, 12	A0 – A3	Data inputs
3, 6, 8, 11	Y0 – Y3	Data outputs
1, 4, 10, 13	OE0 - OE3	Output enable inputs
7	GND	Ground (0V)
14	V _{CC}	Positive supply voltage

PIN CONFIGURATION



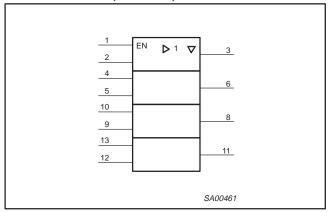
LOGIC SYMBOL



Quad buffer (3-State)

74ABT126

LOGIC SYMBOL (IEEE/IEC)



FUNCTION TABLE

INPU	INPUTS						
OEn	An	Yn					
Н	L	L					
Н	Н	Н					
L	Х	Z					

H = High voltage level

L = Low voltage level

X = Don't care
Z = High impedance "off" state

ABSOLUTE MAXIMUM RATINGS^{1, 2}

SYMBOL	PARAMETER	CONDITIONS	RATING	UNIT
V _{CC}	DC supply voltage		-0.5 to +7.0	V
I _{IK}	DC input diode current	V _I < 0	-18	mA
VI	DC input voltage ³		-1.2 to +7.0	V
lok	DC output diode current	V _O < 0	-50	mA
V _{OUT}	DC output voltage ³	output in Off or High state	-0.5 to +5.5	V
lout	DC output current	output in Low state	128	mA
T _{stg}	Storage temperature range		-65 to 150	°C

NOTES:

- 1. Stresses beyond those listed may cause permanent damage to the device. These are stress ratings only and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to
- absolute-maximum-rated conditions for extended periods may affect device reliability.

 2. The performance capability of a high-performance integrated circuit in conjunction with its thermal environment can create junction temperatures which are detrimental to reliability. The maximum junction temperature of this integrated circuit should not exceed 150°C.

 3. The input and output voltage ratings may be exceeded if the input and output current ratings are observed.

RECOMMENDED OPERATING CONDITIONS

CYMPOL	PARAMETER	LIM	ITS	LINUT
SYMBOL	PARAMETER	Min	Max	UNIT
V _{CC}	DC supply voltage	4.5	5.5	V
VI	Input voltage	0	V _{CC}	V
V _{IH}	High-level input voltage	2.0		V
V _{IL}	Low-level Input voltage		0.8	V
I _{OH}	High-level output current		-32	mA
I _{OL}	Low-level output current		64	mA
Δt/Δν	Input transition rise or fall rate	0	10	ns/V
T _{amb}	Operating free-air temperature range	-40	+85	°C

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DC ELECTRICAL CHARACTERISTICS

					LIMITS			
SYMBOL	PARAMETER	TEST CONDITIONS	Tai	_{nb} = +25	s∘C	T _{amb} =	-40°C 85°C	UNIT
			Min	Тур	Max	Min	Max	
V _{IK}	Input clamp voltage	$V_{CC} = 4.5V; I_{IK} = -18mA$		-0.9	-1.2		-1.2	V
		$V_{CC} = 4.5V$; $I_{OH} = -3mA$; $V_I = V_{IL}$ or V_{IH}	2.5	2.9		2.5		V
V _{OH}	High-level output voltage	$V_{CC} = 5.0V$; $I_{OH} = -3mA$; $V_I = V_{IL}$ or V_{IH}	3.0	3.4		3.0		V
		$V_{CC} = 4.5V$; $I_{OH} = -32mA$; $V_I = V_{IL}$ or V_{IH}	2.0	2.4		2.0		V
V _{OL}	Low-level output voltage	$V_{CC} = 4.5V$; $I_{OL} = 64mA$; $V_I = V_{IL}$ or V_{IH}		0.35	0.55		0.55	V
I _I	Input leakage current	$V_{CC} = 5.5V; V_I = GND \text{ or } 5.5V$		±0.01	±1.0		±1.0	μΑ
I _{OFF}	Power-off leakage current	$V_{CC} = 0.0V$; V_O or $V_I \le 4.5V$		±5.0	±100		±100	μΑ
I _{PU} /I _{PD}	Power-up/down 3-State output current ³	$V_{\underline{CC}}$ = 2.1V; $V_{\underline{O}}$ = 0.5V; $V_{\underline{I}}$ GND or $V_{\underline{CC}}$; $V_{\underline{OE}}$ = Don't care		±5.0	±50		±50	μА
I _{OZH}	3-State output High current	$V_{CC} = 5.5V; V_O = 2.7V; V_I = V_{IL} \text{ or } V_{IH}$		1.0	50		50	μΑ
I _{OZL}	3-State output Low current	$V_{CC} = 5.5V$; $V_{O} = 0.5V$; $V_{I} = V_{IL}$ or V_{IH}		-1.0	-50		-50	μΑ
I _{CEX}	Output High leakage current	V_{CC} = 5.5V; V_{O} = 5.5V; V_{I} = GND or V_{CC}		5.0	50		50	μΑ
Io	Output current ¹	$V_{CC} = 5.5V; V_O = 2.5V$	-50	-100	-180	-50	-180	mA
Іссн		$V_{CC} = 5.5V$; Outputs High, $V_I = GND$ or V_{CC}		65	250		250	μΑ
I _{CCL}	Quiescent supply current	$V_{CC} = 5.5V$; Outputs Low, $V_I = GND$ or V_{CC}		12	15		15	mA
I _{CCZ}		V_{CC} = 5.5V; Outputs 3–State; V_{I} = GND or V_{CC}		65	250		250	μА
		Outputs enabled, one data input at 3.4V, other inputs at V_{CC} or GND; V_{CC} = 5.5V		0.5	1.5		1.5	mA
Δl _{CC}	Additional supply current per input pin ²	Outputs 3-State, one data input at 3.4V, other inputs at V_{CC} or GND; V_{CC} = 5.5V		50	250		250	μА
NOTES:		Outputs 3-State, one enable input at 3.4V, other inputs at V_{CC} or GND; $V_{CC} = 5.5V$		0.5	1.5		1.5	mA

- NOTES:

 1. Not more than one output should be tested at a time, and the duration of the test should not exceed one second.
- This is the increase in supply current for each input at 3.4V.
 This parameter is valid for any V_{CC} between 0V and 2.1V, with a transition time of up to10msec. From V_{CC} = 2.1V to V_{CC} = 5V ± 10%, a transition time of up to 100μsec is permitted.

AC CHARACTERISTICS

GND = 0V; $t_R = t_F$ = 2.5ns; C_L = 50pF, R_L = 500 Ω

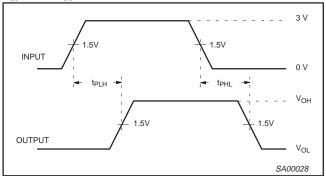
SYMBOL	PARAMETER	WAVEFORM	T _a	_{imb} = +25° 'CC = +5.0'	C V	T _{amb} = -40° V _{CC} = +5.	UNIT	
			Min	Тур	Max	Min	Max	
t _{PLH} t _{PHL}	Propagation delay An to Yn	1	1.0 1.0	2.9 3.0	4.2 4.3	1.0 1.0	4.4 4.6	ns
t _{PZH}	Output enable time to High and Low level	2	1.9 1.9	3.2 4.4	5.8 5.9	1.9 1.9	6.5 6.5	ns
t _{PHZ} t _{PLZ}	Output disable time from High and Low level	2	1.0 1.0	4.2 2.9	5.2 4.9	1.0 1.0	5.8 5.5	ns

Quad buffer (3-State)

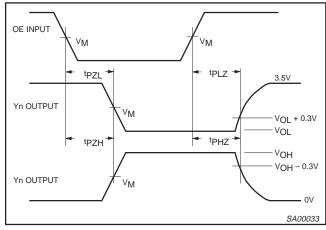
74ABT126

AC WAVEFORMS

 $V_{M} = 1.5V, V_{IN} = GND \text{ to } 3.0V$

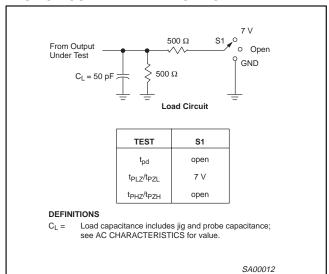


Waveform 1. Waveforms Showing the Input (An) to Output (Yn) Propagation Delays



Waveform 2. Waveforms Showing the 3-State Output Enable and Disable Times

TEST CIRCUIT AND WAVEFORMS



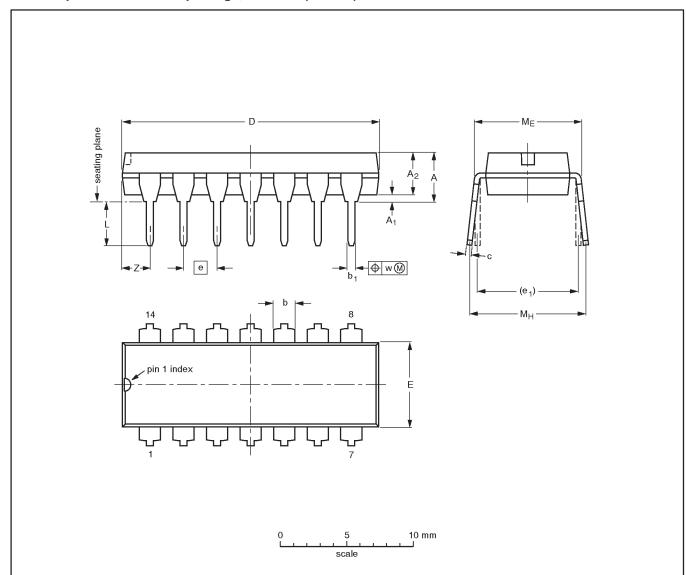
1998 Jan 16 5

Quad buffer (3-State)

74ABT126

DIP14: plastic dual in-line package; 14 leads (300 mil)

SOT27-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

	· •														
UNIT	A max.	A ₁ min.	A ₂ max.	b	b ₁	С	D ⁽¹⁾	E (1)	е	e ₁	L	ME	Мн	w	Z ⁽¹⁾ max.
mm	4.2	0.51	3.2	1.73 1.13	0.53 0.38	0.36 0.23	19.50 18.55	6.48 6.20	2.54	7.62	3.60 3.05	8.25 7.80	10.0 8.3	0.254	2.2
inches	0.17	0.020	0.13	0.068 0.044	0.021 0.015	0.014 0.009	0.77 0.73	0.26 0.24	0.10	0.30	0.14 0.12	0.32 0.31	0.39 0.33	0.01	0.087

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE			
VERSION	IEC JEDEC EIAJ				PROJECTION	ISSUE DATE	
SOT27-1	050G04	MO-001AA				92-11-17 95-03-11	

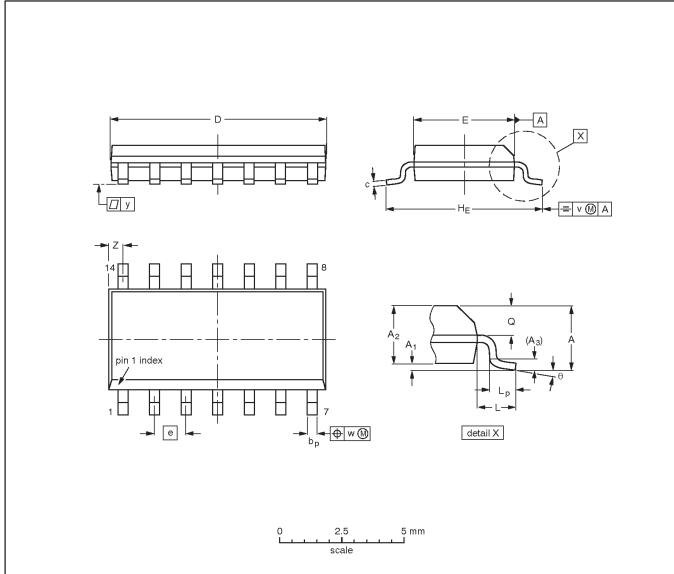
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Quad buffer (3-State)

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SO14: plastic small outline package; 14 leads; body width 3.9 mm

SOT108-1



DIMENSIONS (inch dimensions are derived from the original mm dimensions)

UNIT	A max.	A ₁	A ₂	А3	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	٦	Lp	Q	>	w	у	Z ⁽¹⁾	θ
mm	1.75	0.25 0.10	1.45 1.25	0.25	0.49 0.36	0.25 0.19	8.75 8.55	4.0 3.8	1.27	6.2 5.8	1.05	1.0 0.4	0.7 0.6	0.25	0.25	0.1	0.7 0.3	8°
inches	0.069	0.010 0.004	0.057 0.049	0.01		0.0100 0.0075		0.16 0.15	0.050	0.244 0.228	0.041	0.039 0.016		0.01	0.01	0.004	0.028 0.012	0°

Note

1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT108-1	076E06S	MS-012AB				95-01-23 97-05-22

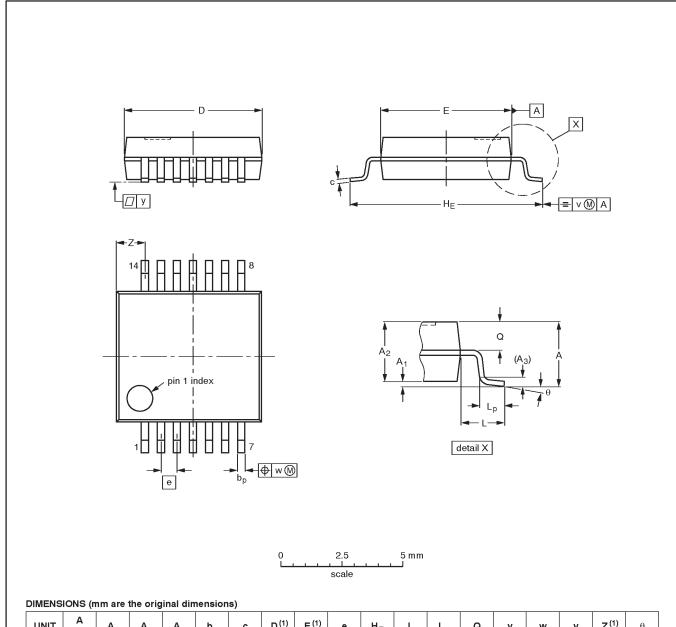
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Quad buffer (3-State)

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SSOP14: plastic shrink small outline package; 14 leads; body width 5.3 mm

SOT337-1



UNIT	A max.	A ₁	A ₂	A ₃	bp	С	D ⁽¹⁾	E ⁽¹⁾	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
mm	2.0	0.21 0.05	1.80 1.65	0.25	0.38 0.25	0.20 0.09	6.4 6.0	5.4 5.2	0.65	7.9 7.6	1.25	1.03 0.63	0.9 0.7	0.2	0.13	0.1	1.4 0.9	8° 0°

Note

1. Plastic or metal protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	RENCES	EUROPEAN ISSUE DATE				
VERSION	IEC	JEDEC	EIAJ	PROJECTION	ISSUE DATE			
SOT337-1		MO-150AB			-95-02-04 96-01-18			

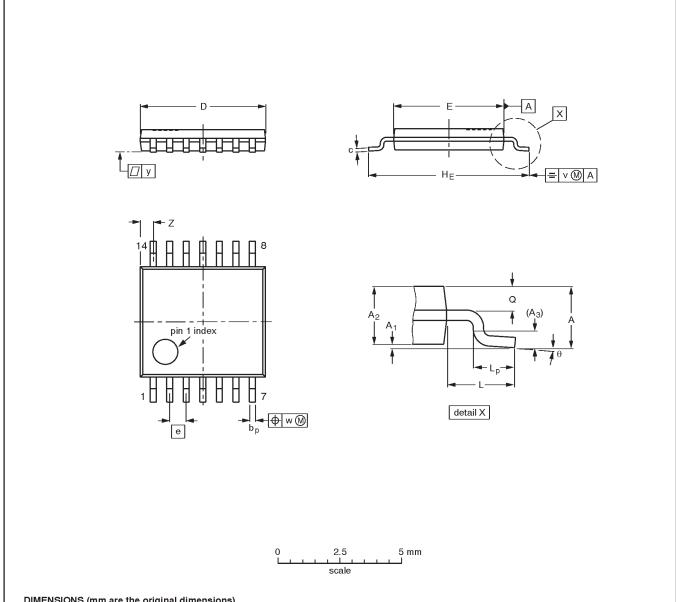
Product specification Philips Semiconductors

Quad buffer (3-State)

74ABT126

TSSOP14: plastic thin shrink small outline package; 14 leads; body width 4.4 mm

SOT402-1



DIMENSIONS (mm are the original dimensions)

Г	UNIT	A max.	Α1	A ₂	A ₃	bp	С	D ⁽¹⁾	E (2)	е	HE	L	Lp	Q	v	w	у	Z ⁽¹⁾	θ
	mm	1.10	0.15 0.05	0.95 0.80	0.25	0.30 0.19	0.2 0.1	5.1 4.9	4.5 4.3	0.65	6.6 6.2	1.0	0.75 0.50	0.4 0.3	0.2	0.13	0.1	0.72 0.38	8° 0°

Notes

- 1. Plastic or metal protrusions of 0.15 mm maximum per side are not included.
- 2. Plastic interlead protrusions of 0.25 mm maximum per side are not included.

OUTLINE		REFER	EUROPEAN	ISSUE DATE		
VERSION	IEC	JEDEC	EIAJ		PROJECTION	ISSUE DATE
SOT402-1		MO-153				-94-07-12 95-04-04

Quad buffer (3-State)

74ABT126

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Data Sheet Identification	Product Status	Definition					
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